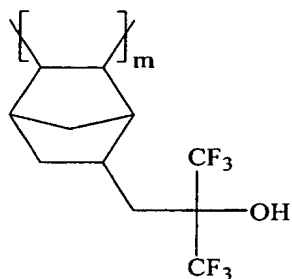


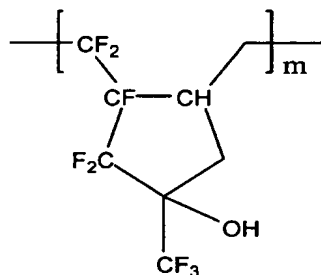
In the Claims:

1. (Currently Amended) A light absorption depressant comprising:
a TIMD (~~tetra~~isopropyl tetraisopropyl methylene diphosphonate) which depresses light absorption at a wavelength of less than 200nm.
2. (Original) The light absorption depressant according to claim 1, wherein the wavelength is 157 nm or 193 nm.
3. (Currently Amended) A photoresist composition comprising a TIMD (~~tetra~~isopropyl tetraisopropyl methylene diphosphonate).
4. (Original) The photoresist composition according to claim 3 further comprising a base resin and wherein the TIMD is present in an amount ranging from 0.01 to 25 wt% based on the base resin.
5. (Original) The photoresist composition according to claim 4, wherein the TIMD is present in an amount ranging from 0.01 to 20 wt% based on the base resin.
6. (Original) The photoresist composition according to claim 3, wherein the TIMD is added in the photoresist composition for a 157 nm light source or for a 193 nm light source.
7. (Original) The photoresist composition according to claim 3, which comprises (1) a poly(norbornenehexafluoroalcohol) represented by Formula 2 or (2) a blend polymer of polymers represented by Formula 3a and Formula 3b as a base resin.

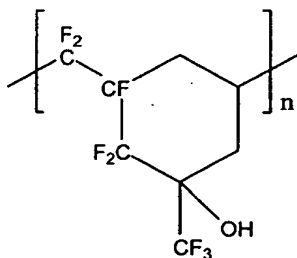
Formula 2



Formula 3a



Formula 3b



8. (Original) The photoresist composition according to claim 7, wherein the composition is a chemically amplified photoresist composition comprising a photoacid generator.

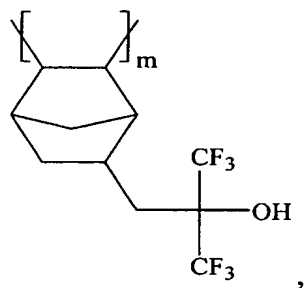
9. (Original) A process for forming a photoresist pattern, comprising:
- (a) coating the photoresist composition of claim 3 on an underlying layer to form a photoresist film;
 - (b) baking the photoresist film, and then exposing the baked photoresist film to light;
 - (c) baking the exposed photoresist film; and
 - (d) developing the baked photoresist film to obtain a photoresist pattern.

10. (Original) A semiconductor device manufactured according to the process of claim 9.

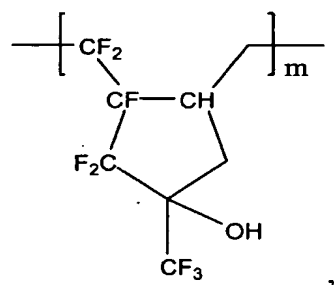
11. (Cancelled)

12. (Currently Amended) A photoresist composition comprising a TIMD (~~tetra~~isopropyl ~~propyl~~ tetraisopropyl methylene diphosphonate) and a base resin selected from the group consisting of

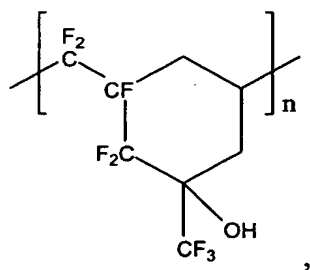
Formula 2



Formula 3a



Formula 3b



and mixtures thereof.

13. (Original) The photoresist composition according to claim 12, wherein the TIMD is present in an amount ranging from 0.01 to 25 wt% based on the base resin.

14. (Original) The photoresist composition according to claim 13, wherein the TIMD is present in an amount ranging from 0.01 to 20 wt% based on the base resin.

15. (Original) The photoresist composition according to claim 12, wherein the TIMD is added in the photoresist composition for a 157 nm light source or for a 193 nm light source.

16. (Original) The photoresist composition according to claim 15, wherein the composition is a chemically amplified photoresist composition comprising a photoacid generator.

17. (Original) A process for forming a photoresist pattern, comprising:
(a) coating the photoresist composition of claim 12 on an underlying layer to form a photoresist film;
(b) baking the photoresist film, and then exposing the baked photoresist film to light;
(c) baking the exposed photoresist film; and
(d) developing the baked photoresist film to obtain a photoresist pattern.

18. (Original) The photoresist composition according to claim 12 further comprising a hydrocarbon compound including P=O groups.

19. (Original) A semiconductor device manufactured according to the process of claim 17.